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LED570-66-60

TECHNICAL DATA



High Power LED Array, 60 chips

InGaAIP

LED570-66-60 is a wide viewing and extremely high output power illuminator assembled with a total of 60 high efficiency InGaAIP diode chips, mounted on a metal stem TO-66 with AIN ceramics and covered with double coated clear silicone and epoxy resin.

These devices are designed for high current operation with proper heat sinking to improver thermal conductive efficiency.

Specifications

Structure: InGaAIP, 60 LED chips
Peak Wavelength: typ. 570 nm
Optical Output Power: typ. 36 mW

Package: TO-66 stem with AIN,

clear epoxy resin

Absolute Maximum Ratings (T_C=25°C)

Item	Symbol	Value	Unit
Power Dissipation	P_{D}	4.5	W
Forward Current	I _F	400	mΑ
Pulsed Forward Current *1	I _{FP}	600	mΑ
Reverse Voltage	V_R	50	V
Operating Temperature	T_{opr}	-30 +85	ဂိ
Storage Temperature	T_{stg}	-30 +110	ဂိ
Soldering Temperature *2	T _{sol}	265	°C

 $^{^{*1}}$ duty = 1%, pulse width = 1 μ s

31.50 24.38 2-\varphi 3.58 2-\varphi 3.58 2-\varphi 1.5 10.91 \text{A node} \tilde{\text{Cathode}} \text{Cathode}



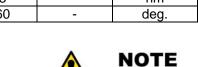
Electro-Optical Characteristics

Item	Symbol	Condition	Min.	Тур.	Max.	Unit
Total Radiated Power	Po	$I_F = 240 \text{ mA}$	ı	36	-	mW
Brightness	I_{V}	$I_F = 240 \text{ mA}$	1	7.0	-	cd
Forward Voltage	V_{F}	$I_F = 240 \text{ mA}$	-	11.0	-	V
Reverse Voltage	V_R	$I_R = 10 \mu A$	50	-	-	V
Peak Wavelength	λ_{P}	$I_F = 240 \text{ mA}$	560	570	580	nm
Half Width	Δλ	$I_F = 240 \text{ mA}$	-	15	-	nm
Viewing Half Angle	Θ _{1/2}	$I_F = 240 \text{ mA}$	-	±60	-	deg.

Heat Sink is required, thermal resistance <8K/W

Notes

- This high power LED must be cooled!
- Do not view directly into the emitting area of the LED during operation!
- The above specifications are for reference purpose only and subjected to change without prior notice.



^{*2} must be completed within 3 seconds